

Data sheet acquired from Harris Semiconductor SCHS020

CMOS Hex Buffers/Converters

High-Voltage Types (20-Volt Rating)

Inverting Type: CD4009UB Non-Inverting Type: CD4010B

■ CD4009UB and CD4010B Hex Buffer/Converters may be used as CMOS to TTL or DTL logic-level converters or CMOS high-sink-current drivers.

The CD4049UB and CD4050B are preferred hex buffer replacements for the CD4009UB and CD4010B, respectively, in all applications except multiplexers. For applications not requiring high sink current or voltage conversion, the CD4069UB Hex Inverter is recommended.

The CD4009UB and CD4010B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

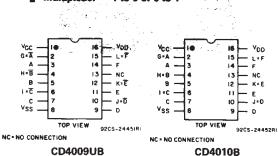
CD4009UB, CD4010B Types

Features:

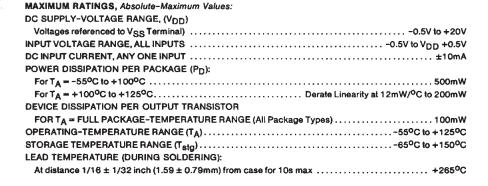
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings

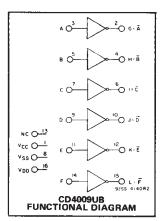
Applications:

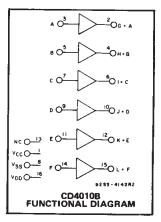
- CMOS to DTL/TTL hex converter
- CMOS current "sink" or "source" driver
- CMQS high-to-low logic-level converter
- Multiplexer 1 to 6 or 6 to 1



TERMINAL ASSIGNMENTS







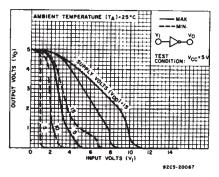


Fig. 3 — Minimum and maximum voltage transfer characteristics—CD4009UB.

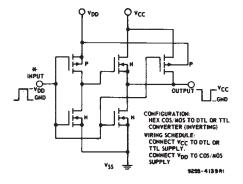


Fig. 1 — Schematic diagram of CD4009UB— 1 of 6 identical stages.

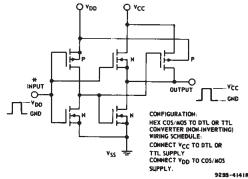
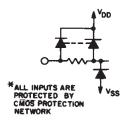


Fig. 2 — Schematic diagram of CD4010B— 1 of 6 identical stages.



CD4009UB, CD4010B Types

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS			
CHARACTERISTIC	MIN. MAX.		UNITS	
Supply-Voltage Range (For TA = Full				
Package Temperature Range), VDD	3	18	V	
Vcc*	3	V _{DD}	1	
Input Voltage Range (V _I)	Vcc*	V _{DD}	٧	

^{*}The CD4009UB and CD4010B have high-to-low level voltage conversion capability but not low-to-high level, therefore it is recommended that $|V_{DD}| \ge |V_I| \ge |V_{CC}|$.

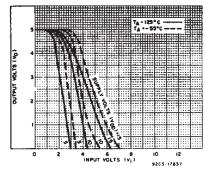


Fig. 4 — Typical voltage transfer characteristics as function of temp.—CD4009UB.

STATIC ELECTRICAL CHARACTERISTICS

CHARAC- TERISTIC	CONDITIONS		LIMITS AT INDICATED TEMPERATURES (°C)						UNITS					
	Vo	VIN	V _{DD}	-55	-40	+85	+125		+25					
	(V)	(V)	(V)					Min.	Тур.	Max.				
Quiescent	L -	0,5	5	1	1	30	30		0.02	1				
Device	_	0,10	10	2	2	60	60	_	0.02	2				
Current, I _{DD}		0,15	15	4	4	120	120		0.02	4	μΑ			
Max.		0,20	20	20	20	600	600		0.04	20				
Output Low	0.4	0,5	4.5	3.2	3.1	2.1	1.8	2.6	3.4					
(Sink)	0.4	0,5	5	3.75	3.6	2.4	2.1	3	4					
Current	0.5	0,10	10	10	9.6	6.4	5.6	8	10	_				
I _{OL} Min.	1.5	0,15	15	30	40	19	16	24	36	-	mA			
Output High	4.6	0,5	5	-0.25	-0.23	-0.18	-0.15	-0.2	-0.4	_	IIIA			
(Source)	2.5	0,5	5	-1	-0.9	-0.65	-0.58	0.8	-1.6	-				
Current	9.5	0,10	10	0.55	-0.5	-0.38	-0.33	-0.45	-0.9					
IOH Min.	13.5	0,15	15	-1.65	-1.6	-1.25	-1.1	-1.5	-3	_				
Output Voltage:	_	0,5	5		0.0	05		_	0	0.05	.05			
Low-Level,	_	0,10	10	0.05				0	0.05					
VOL Max.	<u> </u>	0,15	15		0.0	05		_	0	0.05	_			
Output Voltage:		0,5	5		4.95 9.95			4.95	4.95 5	_				
High-Level,		0,10	10					9.95	10	_				
V _{OH} Min.	_	0,15	15	14.95			14.95	15						
Input Low	4.5	- 5		1					1					
Voltage:	9	_	10			2	-	_		2				
V _{IL} Max. CD4009UB	/IL Max.		15	2.5			_	-	2.5					
Input Low	0.5	_	5		1.5					1.5				
Voltage:	1		10			3				3				
V _{IL} Max. CD4010B	1.5		15	4		-	-	4						
Input High	0.5		5		4			4	_	_	V			
Voltage:	1	i — 11	10	8			8		-					
V _{IH} Min. CD4009UB	1.5	-	15		1:	2.5		12.5		-				
Input High	4.5		5	3.5			3.5							
Voltage:	9	-	10	7			7			1				
V _{IH} Min. CD4010B	13.5	-	15	11			11	_	-					
Input Current, I _{LN} Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μΑ			

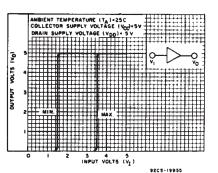


Fig. 5 — Minimum and maximum voltage transfer characteristics (V_{DD}=5)—CD4010B.

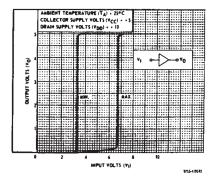


Fig. 6 – Minimum and maximum voltage transfer characteristics (V_{DD} =10)--CD4010B.

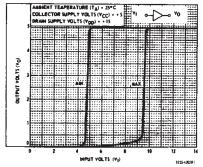


Fig. 7 — Minimum and maximum voltage transfer characteristics (V_{DD}*15)—CD4010B.

CD4009UB, CD4010B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A =25°C; Input t_r , t_f =20 ns, C_L =50 pF, R_L =200 $K\Omega$

		ÖNDITION	s		LIMITS ALL PKGS		
CHARACTERISTIC	V _{DD} (V)	V _I (V)	VCC (V)	TYP.	MAX.	UNIT	
Propagation Delay Time:] _		_				
Low-to-High, tPLH	5	5	5	70	140	1	
	10	10	10	40	- 80		
CD4009UB	10	10	5	35	70	ns	
	15	15	15	30	60		
	15	15	5	30	60		
	5	5	5	100	200		
	10	10	10	50	100		
CD4010B	10	10	5	50	100	ns	
	15	15	15	35	70	1	
	15	15	5	35	70	1	
High-to-Low, tPHL	5	5	5	30	60		
	10	10	10	20	40	1	
CD4009UB	10	10	5	15	30	ns	
	15	15	15	15	30	1	
	15	15	5	10	20		
-	5	5	5	65	130		
	10	10	10	35	70		
CD4010B	10	10	5	30	70	ns	
	15	15	15	25	50		
	15	15	5	20	40		
Transition Time:	!			 			
Low-to-High, tTLH	5	5	5	150	350		
	10	10	10	75	150	ns	
	15	15	15	55	110		
High-to-Low, tTHL	5	5	5	35	70		
	10	10	10	20	40	ns	
	15	15	15	15	30		
Input Capucitance, CIN CD4009UB	_	_	_	15	22.5		
CD4010B	_		_	5	7.5	ρF	

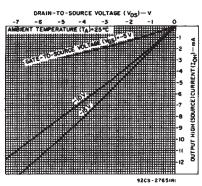


Fig. 11 — Typical output high (source) current characteristics,

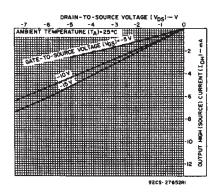


Fig. 12 — Minimum output high (source) current characteristics.

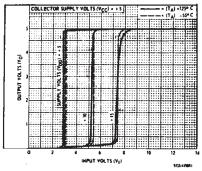


Fig. 8 - Typical voltage transfer characteristics as a function of temperature—CD4010B.

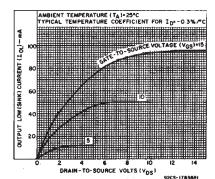


Fig. 9 — Typical output low (sink) current characteristics.

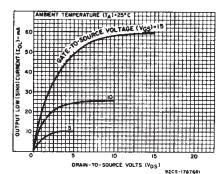


Fig. 10 – Minimum output low (sink) current characteristics.

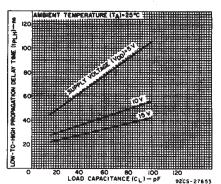


Fig. 13 — Typical low-to-high propagation delay time vs. load capacitance (CD4009UB).

AMBIENT TEMPERATURE (TA)-25°C

Fig. 14 — Typical high-to-low propagation delay time vs. load capacitance (CD4009UB).

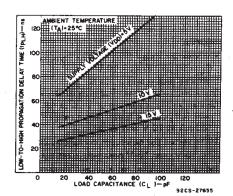


Fig. 15 — Typical low-to-high propagation delay time vs. load capacitance (CD4010B).

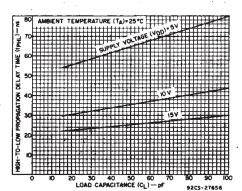


Fig. 16 — Typical-high-to-low propagation delay time vs. load capacitance (CD4010B).

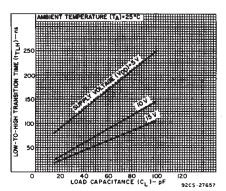


Fig. 17 — Typical low-to-high transition time vs. load capacitance.

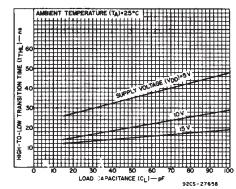


Fig. 18 — Typical high-to-low transition time vs. load capacitance.

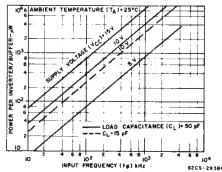


Fig. 19 — Typical dissipation characteristics.

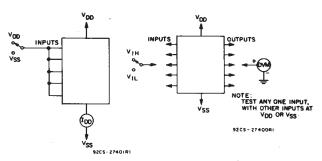
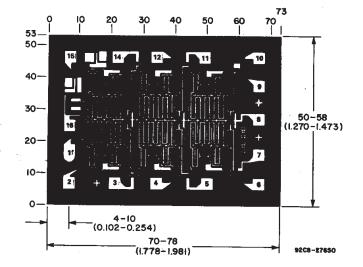


Fig. 20 — Quiescent device current test circuit,

Fig. 21 — Noise immunity test circuit.



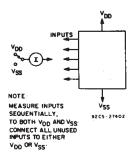


Fig. 22 - Input current test circuit,

Dimensions in parentheses are in millimeters and are derived from the besic inch dimensions as indicated, Grid Graduations Are In Mils (10^{-3} Inch)

Photograph of chip for CD4009UB. Dimensions and pad layout for CD4010B are identical.

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